TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

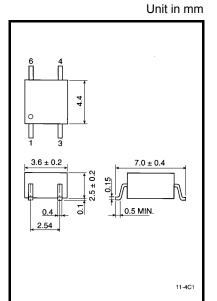
TLP126

Programmable Controllers AC / DC-Input Module Telecommunication

The TOSHIBA mini flat coupler TLP126 is a small outline coupler, suitable for surface mount assembly.

TLP126 consists of a photo transistor, optically coupled to a gallium arsenide infrared emitting diode connected inverse parallel, and provides high CTR at low AC input current.

- Collector-emitter voltage: 80 V (min.)
- Current transfer ratio: 100% (min.)
- Isolation voltage: 3750Vrms (min.)
- UL recognized: UL1577, file No. E67349

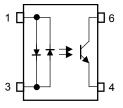


Weight: 0.09 g

TOSHIBA

Pin Configurations (top view)

11-4C1



- 1: Anode, Cathode
- 3 : Cathode, Anode
- 4 : Emitter
- 6: Collector

Absolute Maximum Ratings (Ta = 25°C)

| | Characteristic | Symbol | Rating | Unit |
|----------|---|----------------------|---------|---------|
| | Forward current | I _{F(RMS)} | 50 | mA |
| Ω | Forward current derating (Ta≥ 53°C) Δ | ΔI _F / °C | -0.7 | mA / °C |
| LED | Peak forward current(100µs pulse,100pps) | I _{FP} | 1 | Α |
| | Junction temperature | Tj | 125 | °C |
| | Collector-emitter voltage | V _{CEO} | 80 | ٧ |
| | Emitter-collector voltage | V _{ECO} | 7 | ٧ |
| ō | Collector current | IC | 50 | mA |
| Detector | Peak collector current(10ms pulse,100pps) | I _{CP} | 100 | mA |
| ۵ | Power dissipation | PC | 150 | mW |
| | Power dissipation derating (Ta ≥ 25°C) | ΔP _C / °C | -1.5 | mW / °C |
| | Junction temperature | Tj | 125 | °C |
| Stor | age temperature range | T _{stg} | -55~125 | °C |
| Ope | rating temperature range | T _{opr} | -55~100 | °C |
| Lea | d soldering temperature(10 sec.) | T _{sold} | 260 | °C |
| Tota | al package power dissipation | PT | 200 | mW |
| Tota | al package power dissipation derating (Ta≥25°C) | ΔP _T / °C | -2.0 | mW / °C |
| Isola | ation voltage (AC, 1min., RH ≤ 60%) (Note 1) | BVS | 3750 | Vrms |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 1) Device considered a two terminal device: Pins1, and 3 shorted together and 4 and 6 shorted together.

Recommended Operating Conditions

| Characteristic | Symbol | Min. | Тур. | Max. | Unit |
|-----------------------|---------------------|------|------|------|------|
| Supply voltage | V _{CC} | _ | 5 | 48 | V |
| Forward current | I _{F(RMS)} | _ | 1.6 | 20 | mA |
| Collector current | IC | _ | 1 | 10 | mA |
| Operating temperature | T _{opr} | -25 | _ | 75 | °C |

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

Individual Electrical Characteristics (Ta = 25°C)

| | Characteristic | Symbol | Test Condition | Min. | Тур. | Max. | Unit |
|----------|-------------------------------------|-----------------------|-----------------------------------|------|------|------|------|
| LED | Forward voltage | V_{F} | I _F = ±10 mA | 1.0 | 1.15 | 1.3 | V |
| ILE | Capacitance | C _T | V = 0, f = 1 MHz | | 60 | _ | pF |
| Detector | Collector–emitter breakdown voltage | V _(BR) CEO | I _C = 0.5 mA | 80 | _ | | ٧ |
| | Emitter-collector breakdown voltage | V _(BR) ECO | I _E = 0.1 mA | 7 | _ | | ٧ |
| | Collector dark current | la-a | V _{CE} = 48 V | _ | 10 | 100 | nA |
| | Collector dark current | ICEO | V _{CE} = 48 V, Ta = 85°C | | 2 | 50 | μΑ |
| | Capacitance collector to emitter | C _{CE} | V = 0, f = 1 MHz | | 12 | _ | pF |

Coupled Electrical Characteristics (Ta = 25°C)

| Characteristic | Symbol | Test Condition | MIn. | Тур. | Max. | Unit |
|-----------------------------|---------------------------------|---|------|------|------|------|
| Current transfer ratio | I _C / I _F | $I_F = \pm 1$ mA, $V_{CE} = 0.5$ V | 100 | _ | 1200 | % |
| Low input CTR | Ic / I _{F (low)} | IF = ±0.5 mA, V _{CE} = 1.5 V | 50 | _ | _ | % |
| Collector-emitter | Vo= () | I _C = 0.5 mA, I _F = ±1 mA | | _ | 0.4 | V |
| saturation voltage | V _{CE (sat)} | I _C = 1 mA, I _F = ±1 mA | _ | 0.2 | - | |
| Off-state collector current | I _{C(off)} | V _F = ± 0.7V, V _{CE} = 48 V | _ | 1 | 10 | μΑ |
| CTR symmetry | I _{C (ratio)} | $I_{C} (I_{F} = -1mA) / I_{C} (I_{F} = 1mA)$ | 0.3 | _ | 3 | _ |

Coupled Electrical Characteristics (Ta = $-25\sim75^{\circ}$ C)

| Characteristic | Symbol | Test Condition | Mln. | Тур. | Max. | Unit |
|------------------------|---------------------------------------|--|------|------|------|------|
| Current transfer ratio | I _C / I _F | I _F = 1 mA, V _{CE} = 0.5 V | 50 | _ | _ | % |
| Low input CTR | I _C / I _{F (low)} | IF = 0.5 mA, V _{CE} = 1.5 V | _ | 50 | _ | % |

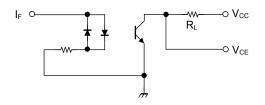
Isolation characteristics (Ta = 25°C)

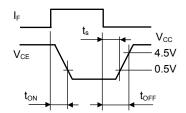
| Characteristic | Symbol | Test Condition | Min. | Тур. | Max. | Unit |
|-----------------------------|----------------|--------------------------------------|--------------------|------------------|------|--------|
| Capacitance input to output | CS | V _S = 0, f = 1 MHz | _ | 0.8 | _ | pF |
| Isolation resistance | R _S | V _S = 500 V | 5×10 ¹⁰ | 10 ¹⁴ | _ | Ω |
| | | AC, 1 minute | 3750 | _ | _ | Vrms |
| Isolation voltage | BV_S | BV _S AC, 1 second, in oil | _ | 10000 | _ | VIIIIS |
| | | DC, 1 minute, in oil | _ | 10000 | _ | Vdc |

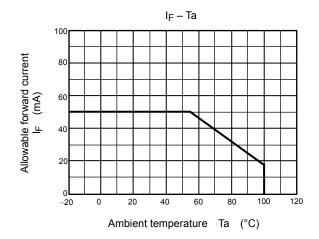
Switching Characteristics (Ta = 25°C)

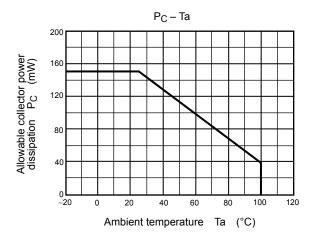
| Characteristic | Symbol | Test Condition | Min. | Тур. | Max. | Unit |
|----------------|------------------|---|------|------|------|------|
| Rise time | t _r | V _{CC} = 10 V, I _C = 2 mA | _ | 8 | _ | |
| Fall time | t _f | | _ | 8 | _ | μs |
| Turn-on time | t _{on} | $R_L = 100\Omega$ | _ | 10 | _ | μδ |
| Turn-off time | t _{off} | | _ | 8 | _ | |
| Turn-on time | t _{ON} | | _ | 10 | _ | |
| Storage time | ts | $R_L = 4.7 \text{ k}\Omega$ (Fig.1) $V_{CC} = 5 \text{ V}, I_F = \pm 1.6 \text{ mA}$ | _ | 50 | _ | μs |
| Turn-off time | tOFF | | _ | 300 | _ | |

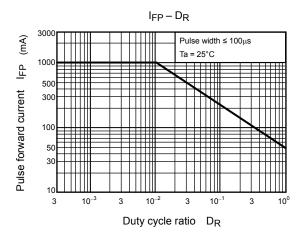
Fig. 1 Switching time test circuit

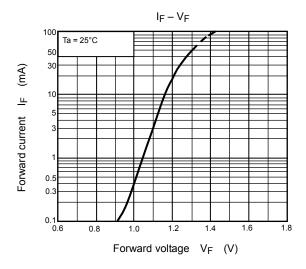


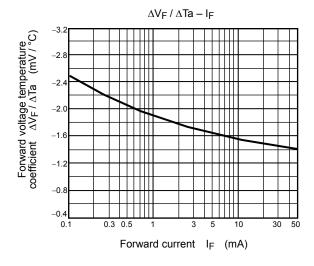


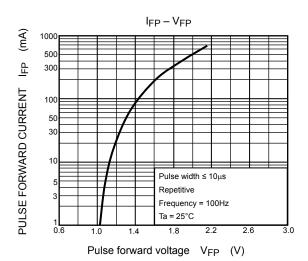


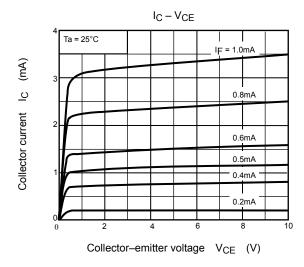


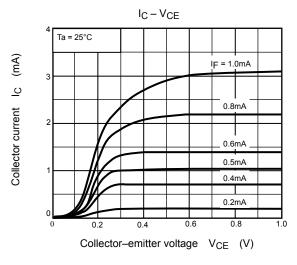


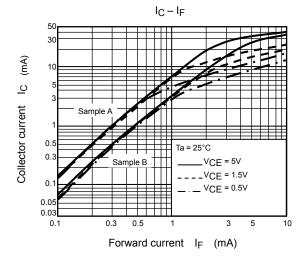


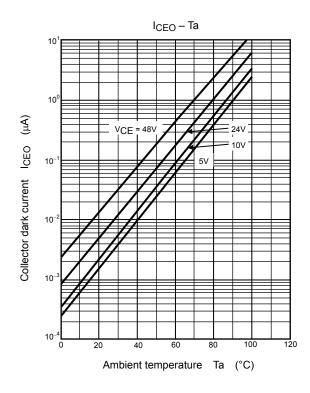


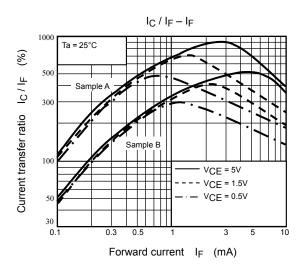




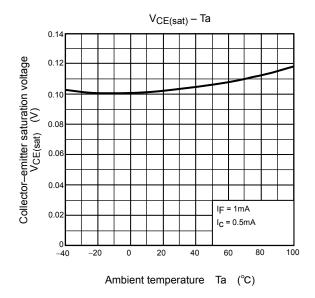


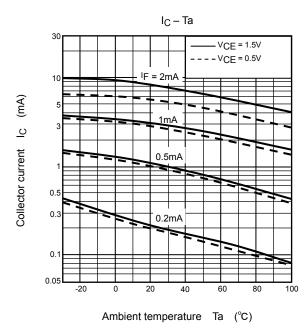


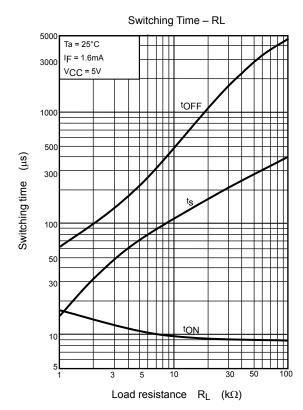




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